www.DataSheet4LLcom

# **S75NS-N**

S29NS-N: MirrorBit<sup>™</sup> 1.8 Volt-only Simultaneous Read/ Write, Burst-mode Multiplexed Flash (NOR Interface)

S30MS-P: ORNAND™ Flash (NAND interface)

**Multiplexed Synchronous pSRAM** 

Data Sheet (Advance Information)



**Notice to Readers:** This document states the current technical specifications regarding the Spansion product(s) described herein. Each product described herein may be designated as Advance Information, Preliminary, or Full Production. See *Notice On Data Sheet Designations* for definitions.



### **Notice On Data Sheet Designations**

Spansion LLC issues data sheets with Advance Information or Preliminary designations to advise readers of product information or intended specifications throughout the product life cycle, including development, qualification, initial production, and full production. In all cases, however, readers are encouraged to verify that they have the latest information before finalizing their design. The following descriptions of Spansion data sheet designations are presented here to highlight their presence and definitions.

### **Advance Information**

The Advance Information designation indicates that Spansion LLC is developing one or more specific products, but has not committed any design to production. Information presented in a document with this designation is likely to change, and in some cases, development on the product may discontinue. Spansion LLC therefore places the following conditions upon Advance Information content:

"This document contains information on one or more products under development at Spansion LLC. The information is intended to help you evaluate this product. Do not design in this product without contacting the factory. Spansion LLC reserves the right to change or discontinue work on this proposed product without notice."

### **Preliminary**

The Preliminary designation indicates that the product development has progressed such that a commitment to production has taken place. This designation covers several aspects of the product life cycle, including product qualification, initial production, and the subsequent phases in the manufacturing process that occur before full production is achieved. Changes to the technical specifications presented in a Preliminary document should be expected while keeping these aspects of production under consideration. Spansion places the following conditions upon Preliminary content:

"This document states the current technical specifications regarding the Spansion product(s) described herein. The Preliminary status of this document indicates that product qualification has been completed, and that initial production has begun. Due to the phases of the manufacturing process that require maintaining efficiency and quality, this document may be revised by subsequent versions or modifications due to changes in technical specifications."

### Combination

Some data sheets contain a combination of products with different designations (Advance Information, Preliminary, or Full Production). This type of document distinguishes these products and their designations wherever necessary, typically on the first page, the ordering information page, and pages with the DC Characteristics table and the AC Erase and Program table (in the table notes). The disclaimer on the first page refers the reader to the notice on this page.

### Full Production (No Designation on Document)

When a product has been in production for a period of time such that no changes or only nominal changes are expected, the Preliminary designation is removed from the data sheet. Nominal changes may include those affecting the number of ordering part numbers available, such as the addition or deletion of a speed option, temperature range, package type, or  $V_{IO}$  range. Changes may also include those needed to clarify a description or to correct a typographical error or incorrect specification. Spansion LLC applies the following conditions to documents in this category:

"This document states the current technical specifications regarding the Spansion product(s) described herein. Spansion LLC deems the products to have been in sufficient production volume such that subsequent versions of this document are not expected to change. However, typographical or specification corrections, or modifications to the valid combinations offered may occur."

Questions regarding these document designations may be directed to your local AMD or Fujitsu sales office.

**S75NS-N** May 3, 2006 S75NS-N\_00-01E

# **S75NS-N**

S29NS-N: MirrorBit<sup>™</sup> 1.8 Volt-only Simultaneous Read/Write, Burst-mode Multiplexed Flash (NOR Interface) S30MS-P: ORNAND<sup>™</sup> Flash (NAND interface) Multiplexed Synchronous pSRAM



Data Sheet (Advance Information)

### **Features**

- Power supply voltage of 1.7 V to 1.95 V
- Burst Speed: 66 MHz

- Package MCP BGA: 0.5 mm ball pitch
  - 11 x 13 x 1.4 mm, 112 ball
- Operating Temperature
  - Wireless, -25°C to +85°C

# **General Description**

The S75NS-N Series is a product line of stacked Multi-Chip Product (MCP) packages and consists of the following items:

- S29NS-N
- S30MS-P
- Mux pSRAM

The products covered by this document are listed in the tables below.

pSRAM	
S29NS128 +	32 Mb
S30MS512P	S75NS128NBF
S30MS01GP	S75NS128NBG

### Product Selector Guide

Device	pSRAM Density	pSRAM Type
S75NS128NBF	32 Mb	Multiplexed pSRAM Type 3
S75NS128NBG	32 Mb	Multiplexed pSRAM Type 3

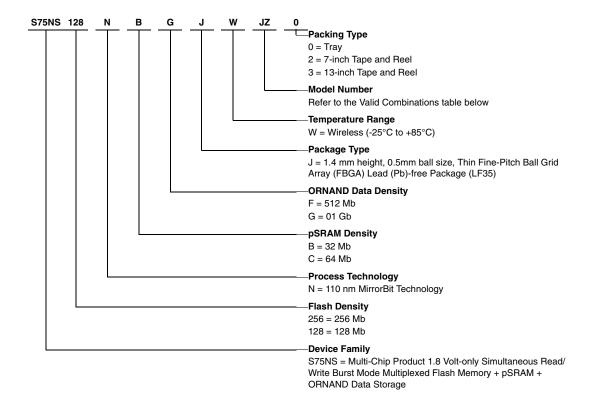
For detailed specifications, please refer to the individual data sheets:

Document	Publication Identification Number	
S29NS-N	S29NS-N_00	
S30MS-P	S30MS-P_00	
32 Mb Multiplexed pSRAM Type 3	muxpsram_04	



# 1. Ordering Information

The ordering part number is formed by a valid combination of the following:



### 1.1 Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult your local sales office to confirm availability of specific valid combinations and to check on newly released combinations.

Table 1.1 MCP Configurations and Valid Combinations

Base Ordering Part Number (Note 2)	Package & Temperature	Model Number	Packing Type	pSRAM Type	Flash Speed Options	pSRAM Speed Options
S75NS128NBF	UJW	JZ 0, 2, 3	0.00	pSRAM Type 3	66 MHz	66 MHz
S75NS128NBG	OJVV			0, 2, 3	pSRAM Type 3	66 MHz

### Notes:

- 1. Type 0 is standard. Specify other options as required.
- 2. The package marking omits the leading S and packing type designator from the ordering part number.
- 3. Contact factory for availability of any of the OPNs listed because RAM type availability may vary over time.

**S75NS-N** S75NS-N\_00\_01E May 3, 2006



# 2. Input/Output Descriptions

Table 2.1 identifies the input and output package connections provided on the device.

Table 2.1 Input/Output Descriptions

Symbol	Signal Type	Description	NS (NOR)	pSRAM	MS (ORNAND)
AMAX – A16	Input	Address inputs	Х	Х	
ADQ15 – ADQ0	I/O	Multiplexed Address/Data	Х	Х	
OE#	Input	Output Enable input. Asynchronous relative to CLK for the Burst mode.	х	Х	
WE#	Input	Write Enable input.	Х	Х	
V <sub>SS</sub>	Ground	Ground	Х	Х	
F-RDY / R-WAIT	Output	Ready output. Indicates the status of the Burst read. The WAIT# pin of the pSRAM is tied to RDY.	х	Х	
CLK	Input	Clock input. In burst mode, after the initial word is output, subsequent active edges of CLK increment the internal address counter. Should be at $V_{IL}$ or $V_{IH}$ while in asynchronous mode	X	Х	
AVD#	Input	Address Valid input. Indicates to device that the valid address is present on the address inputs. Low = for asynchronous mode, indicates valid address; for burst mode, causes starting address to be latched. High = device ignores address inputs	х	x	
F-RST#	Input	Hardware reset input. Low = device resets and returns to reading array data	х		
F-WP#	Input	Hardware write protect input. At $V_{\rm IL}$ , disables program and erase functions in the four outermost sectors. Should be at $V_{\rm IH}$ for all other conditions.	×		
F-ACC	Input	Accelerated input. At $V_{HH}$ , accelerates programming; automatically places device in unlock bypass mode. At $V_{IL}$ , disables all program and erase functions. Should be at $V_{IH}$ for all other conditions.	х		
F-CE#	Input	Chip-enable input for Flash. Asynchronous relative to CLK for Burst Mode.	х		
V <sub>CC</sub>	Power	Flash 1.8 Volt-only single power supply	Х	Х	
R-CE1#	Input	Chip-enable input for pSRAM		Х	
R-CRE	Input	Control Register Enable (pSRAM)		Х	
R-V <sub>CC</sub>	Power	pSRAM Power Supply		Х	
R-UB#	Input	Upper Byte Control (pSRAM)		Х	
R-LB#	Input	Lower Byte Control (pSRAM)		Х	
N-CLE	Input	Command Latch Enable			Х
N-ALE	Input	Address Latch Enable			Х
N-CE#	Input	Chip Enable input for ORNAND			Х
N-WE#	Input	Write Enable input			Х
N-RE#	Input	Read Enable input			Х
N-IO0 - N-IO7	I/O	Data Input/Output			Х
N-WP#	Input	Hardware write protect input. At $V_{\rm IL}$ , disables program and erase functions in the four outermost sectors. Should be at $V_{\rm IH}$ for all other conditions.			х
N-RY/BY#	Input	Ready/Busy output			Х
N-PRE	Input	Power-On Read Enable			Х
N-V <sub>SS</sub>	Ground	Ground			Х
N-V <sub>CC</sub>	Power	ORNAND 1.8 Volt-only single power supply.			Х
DNU	_	Do Not Use			
NC	_	No Connect; not connected internally			



## 3. MCP Block Diagram

A21-A22 A21-A22 F-RST# RST# A15-A0 ADQ15-ADQ0 DQ15-DQ0 F-ACC ACC CLK CLK F-WP# WP# Mux RDY F-RDY/R-WAIT F-CE# CE# **FLASH** OF# OF# WE# WE# **MEMORY** A16-A20 A16-A20 AVD# AVD# VCC VCC VSS VSS VCCQ VCCQ VSSQ VSSQ R-UB# UB# A15-A0 DQ15-DQ0 R-LB# LB# CLK **Mux Sync** WAIT R-CE1# CE# **pSRAM** OE# WE# **MEMORY** A16-A20 AVD# R-CRE CRE VCC VSS VCCQ VSSQ 1/00-1/07 N-IO0 - N-IO7 N-RY/BY# RB# N-PRE PRE CLE **x8 ORNAND** N-CLE N-CE# CE# **Flash** N-ALE ALE VSS N-VSS Memory N-RE# RE# N-WP# WP# VCC N-VCC N-WF# WF#

Figure 3.1 MCP Block Diagram

# 4. Connection Diagrams/Physical Dimensions

This section contains the I/O designations and package specifications for the S71NS-N.

# 4.1 Special Handling Instructions for FBGA Packages

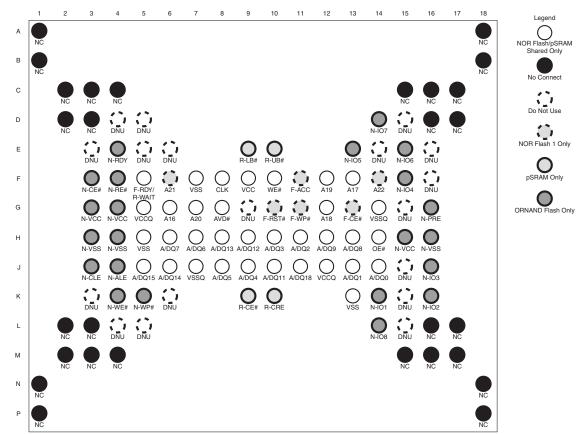
Special handling is required for Flash Memory products in FBGA packages.

Flash memory devices in FBGA packages may be damaged if exposed to ultrasonic cleaning methods. The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

**\$75NS-N** \$75NS-N\_00\_01E May 3, 2006



# 4.2 Connection Diagrams



Note:

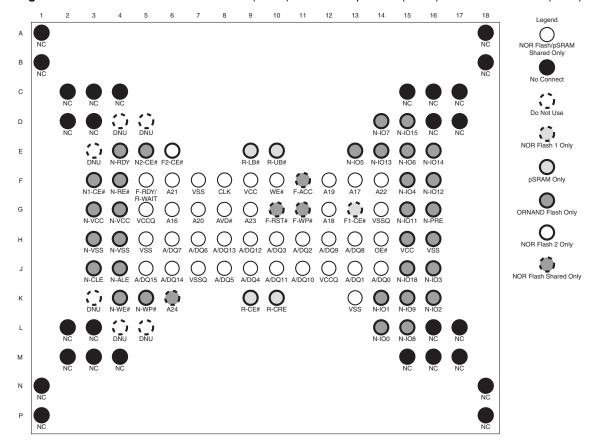
Addresses are shared between Flash and RAM depending on the density of the pSRAM.

MCP	Flash-Only Addresses	Shared Addresses	Shared ADQ Pins
S75NS128NBG	A22-A21	A20-A16	ADQ15 – ADQ0
S75NS128NBF	A22-A21	A20-A16	ADQ15 – ADQ0



## 4.2.1 Lookahead Connection Diagram

Figure 4.1 112-ball x16 MUX NOR FLASH (Bus 1) + x16 MUX pSRAM (Bus 1) + x8/x16 ORNAND (Bus2)



**S75NS-N** S75NS-N\_00\_01E May 3, 2006



#### 4.3 **Physical Dimensions**

A PIN A1 D1 CORNER PIN A1 eD CORNER INDEX MARK SE /7 Ė E1 еE △ 0.15 C (2X) В **TOP VIEW** ○ 0.15 C SD (2X) **BOTTOM VIEW** A2 // 0.20 C SIDE VIEW ○ 0.08 C C 6 112X Ø b Ø 0.15 M C A B Ø 0.08 M C

Figure 4.2 MMB112—11 x 13 mm, 112-ball VFBGA

PACKAGE	MMB 112			
JEDEC	N/A			
	IN/A			
DxE	13.00 mm x 11.00 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	NOTE
Α			1.40	PROFILE
A1	0.20			BALL HEIGHT
A2	0.94		1.11	BODY THICKNESS
D		13.00 BSC		BODY SIZE
Е	11.00 BSC			BODY SIZE
D1	8.50 BSC			MATRIX FOOTPRINT
E1	6.50 BSC			MATRIX FOOTPRINT
MD	18			MATRIX SIZE D DIRECTION
ME	14			MATRIX SIZE E DIRECTION
n		112		BALL COUNT
Øb	0.25	0.30	0.35	BALL DIAMETER
еE		0.50 BSC		BALL PITCH
eD	0.50 BSC			BALL PITCH
SD/SE	0.25 BSC			SOLDER BALL PLACEMENT
	4P,5A,5B, 5C 8A~8E,8K 10L~10P, 12K~12P,1 14M~14P	3,2E~2K,3A,3B,3N, ,5M,5N,5P,6A~6D, ,*8P,9A~9D,9L~9P 11A~11E,11K~11P  3A~13D,13L~13P, ,15A,15B,15N,15P, 17A,17B,17N,17P,	6L~6P,7A~7E, ,10A~10D, ,12A~12E, 14A~14C, 16A.16B.	DEPOPULATED SOLDER BALLS

### NOTES:

- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE IN MILLIMETERS.
- BALL POSITION DESIGNATION PER JEP95, SECTION 4.3, SPP-010.
- e REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

n IS THE NUMBER OF POPULTED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.



DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.



7 SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = e/2

"+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.



A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.



## 5. Revision History

## 5.1 Revision A (May 3, 2006)

Initial release.

### Colophon

The products described in this document are designed, developed and manufactured as contemplated for general use, including without limitation, ordinary industrial use, general office use, personal use, and household use, but are not designed, developed and manufactured as contemplated (1) for any use that includes fatal risks or dangers that, unless extremely high safety is secured, could have a serious effect to the public, and could lead directly to death, personal injury, severe physical damage or other loss (i.e., nuclear reaction control in nuclear facility, aircraft flight control, air traffic control, mass transport control, medical life support system, missile launch control in weapon system), or (2) for any use where chance of failure is intolerable (i.e., submersible repeater and artificial satellite). Please note that Spansion will not be liable to you and/or any third party for any claims or damages arising in connection with above-mentioned uses of the products. Any semiconductor devices have an inherent chance of failure. You must protect against injury, damage or loss from such failures by incorporating safety design measures into your facility and equipment such as redundancy, fire protection, and prevention of over-current levels and other abnormal operating conditions. If any products described in this document represent goods or technologies subject to certain restrictions on export under the Foreign Exchange and Foreign Trade Law of Japan, the US Export Administration Regulations or the applicable laws of any other country, the prior authorization by the respective government entity will be required for export of those products.

### Trademarks and Notice

The contents of this document are subject to change without notice. This document may contain information on a Spansion product under development by Spansion. Spansion reserves the right to change or discontinue work on any product without notice. The information in this document is provided as is without warranty or guarantee of any kind as to its accuracy, completeness, operability, fitness for particular purpose, merchantability, non-infringement of third-party rights, or any other warranty, express, implied, or statutory. Spansion assumes no liability for any damages of any kind arising out of the use of the information in this document.

Copyright © 2006 Spansion LLC. All Rights Reserved. Spansion, the Spansion logo, MirrorBit, ORNAND, and combinations thereof are trademarks of Spansion LLC. Other names are for informational purposes only and may be trademarks of their respective owners.

**8 S75NS-N** S75NS-N\_00\_01E May 3, 2006